

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A method of treating the surface of a material for an electronic device, comprising irradiating the surface of the material with at least a part of plasma components, while supplying a liquid to the surface of the material, to thereby flatten the surface of the material,

wherein a DC bias, an AC bias, or both a DC bias and an AC bias is applied to the material.

Claim 2 (Original): A method of treating the surface of a material for an electronic device according to claim 1, wherein the material for an electronic device is a substrate for an electronic device.

Claim 3 (Original): A method of treating the surface of a material for an electronic device according to claim 1,

wherein radicals, positive ions or negative ions based on a plasma are selectively supplied onto the surface of the material for an electronic device.

Claim 4 (Original): A method of treating the surface according to claim 1, wherein the liquid is H₂O.

Claim 5 (Original): A method of treating the surface according to claim 3, wherein the radicals are high-speed neutral radicals.

Claim 6 (Withdrawn): A surface-treating apparatus, comprising at least: a processing chamber for placing a material for an electronic device to be treated at a predetermined position therein; material-holding means for holding the material for an electronic device in the processing chamber; liquid-supplying means for supplying a liquid onto the surface of the material for an electronic device; and plasma-processing means for treating the surface of the material for an electronic device with a plasma; whereby the surface of the material can be irradiated with the plasma, while supplying the liquid onto the surface of the material for an electronic device.

Claim 7 (Withdrawn): A surface-treating apparatus according to claim 6, comprising particle selection means for selectively irradiating the surface of the material for an electronic device with at least one kind of those selected from radicals, positive ions and negative ions of the plasma components to be supplied from the plasma-processing means.

Claim 8 (Previously Presented): A method of treating the surface according to claim 4, wherein said flattening is accomplished under a pressure of 10 mTorr to 1520 Torr.

Claim 9 (Previously Presented): A method of treating the surface according to claim 8, wherein said flattening is accomplished under a pressure of 10 mTorr to 760 Torr.

Claim 10 (Previously Presented): A method of treating the surface according to claim 9, wherein said flattening is accomplished under a pressure of about 760 Torr.

Claim 11 (Previously Presented): A method of treating the surface according to claim 1, wherein said flattening is accomplished under a pressure of 10 mTorr to 1520 Torr.

Claim 12 (Previously Presented): A method of treating the surface according to claim 11, wherein said flattening is accomplished under a pressure of 10 mTorr to 760 Torr.

Claim 13 (Previously Presented): A method of treating the surface according to claim 11, wherein said flattening is accomplished under a pressure of about 760 Torr.

Claim 14 (Previously Presented): A method of treating the surface according to claim 13, wherein said liquid is H₂O.

Claim 15 (New): A method of treating the surface of a material for an electronic device according to claim 1, wherein said irradiating comprises irradiating the surface of the material with at least a part of a non-equilibrium plasma components.

Claim 16 (New): A method of treating the surface of a material for an electronic device according to claim 1, further comprising providing said plasma components through a slit electrode having a gap of 0.1-0.5 mm.

Claim 17 (New): A method of treating the surface of a material for an electronic device according to claim 16, wherein said providing comprises providing said plasma components through a knife edge type slit electrode.

Claim 18 (New): A method of treating the surface of a material for an electronic device according to claim 1, wherein said irradiating comprises irradiating the surface of the material with at least a part of a plasma having an electron temperature of 0.5 to 5 [eV] and density of 10^{11} to 10^{16} [cm⁻³].